

### DESCRIPTION

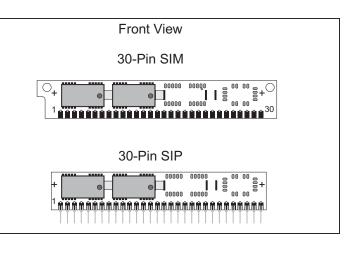
The Accutek AK581024 high density memory modules is a random access memory organized in 1 Meg x 8 bit words. The assembly consists of two 1 Meg x 4 DRAMs in surface mount packages mounted to a printed circuit board. The module can be configured as a leadless 30 pad SIMM or a leaded 30 pin SIP. This packaging approach provides a better than 6 to 1 density increase over standard DIP packaging.

The operation of the AK581024 is identical to two 1 Meg x 4 DRAMs. The data input/output is brought out separately for each 1 Meg x 4 device, with common RAS, CAS and WE control. The OE pins are tied to Vss which dictates the use of early-write cycles to prevent contention of D and Q. Since the Write-Enable (WE) signal must always go low before CAS in a write cycle, Read-Write and Read-Modify-Write operation is not possible.

## **FEATURES**

- 1 Meg x 8 bit organization
- Optional 30 Pad SIM (Single In-Line Module) or 30 Pin leaded SIP (Single In-Line Package)
- JEDEC approved pinout •
- Common CAS, RAS and WE control for eight DQ lines
- Separate CAS control for one separate pair of D and Q lines
- 1024 refresh cycles/16ms, A<sub>0</sub> to A<sub>9</sub>

# AK581024AG / AK581024AS 1,048,576 x 8 bit CMOS **Dvnamic Random Access Memory**



- 1.10 Watt active and 23.5 mWatt standby (max)
- · Operating free air temperature:  $0^0$  to  $70^0$ C
- Upward compatible with AK584096 and AK5816384
- Functionally and Pin compatible with AK481024
- · Available with access times of 60 to 100 nS

# **PIN NOMENCLATURE**

PIN	ASS	GN	MENT

SYMBOL

1/00

DQ1 - DQ8	Data In/Data Out		
		1	
A <sub>0</sub> - A <sub>9</sub>	Address Inputs	2	
CAS	Column Address Strobe	3	
RAS	Row Address Strobe	4	
_		5	
WE	Write Enable	6	
Vcc	5v Supply	7	
Vss	Ground	8	
V 33	Cround	9	
NC	No Connect	10	
		11	
		40	

## **MODULE OPTIONS**

Leadless SIM: AK581024ASP			
Leaded SIP: AK581024AGP			

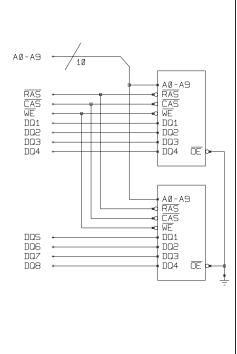
-	1	Vcc	16	DQ5
	2	CAS	17	A8
	3	DQ1	18	A9
_	4	A0	19	NC
_	5	A1	20	DQ6
	6	DQ2	21	WE
	7	A2	22	Vss
	8	A3	23	DQ7
_	9	Vss	24	NC
	10	DQ3	25	DQ8
	11	A4	26	NC
	12	A5	27	RAS
	13	DQ4	28	NC
	14	A6	29	NC
_	15	A7	30	Vcc

PIN #

10

SYMBO

## FUNCTIONAL DIAGRAM



### **ORDERING INFORMATION**

## PART NUMBER CODING INTERPRETATION

Position 2 3 1 Product AK = Accutek Memory 2 Type 4 = Dynamic RAM = CMOS Dynamic RAM 5 6 = Static RAM **Organization/Word Width** 3 1 = by 1 16 = by 16 4 = by 4 32 = by 328 = by 8 36 = by 36 9 = by 9Size/Bits Depth 4 = 64K 64 4096 = 4 MEG 256 = 256K 8192 = 8 MEG 1024 = 1 MEG 16384 = 16 MEG Package Type 5 G = Single In-Line Package (SIP) S = Single In-Line Module (SIM) D = Dual In-Line Package (DIP) W = .050 inch Pitch Edge Connect Z = Zig-Zag In-Line Package (ZIP) 6 Special Designation P = Page Mode N = Nibble Mode K = Static Column Mode W = Write Per Bit Mode V = Video Ram 7 Separator - = Commercial  $0^{0}$ C to +70<sup>0</sup>C M = Military Equivalent Screened  $(-55^{\circ}C to + 125^{\circ}C)$ I = Industrial Temperature Tested  $(-45^{\circ}C \text{ to } +85^{\circ}C)$ X = Burned In 8 Speed (first two significant digits) DRAMS SRAMS 60 = 60 nS12 = 12 nS

 $70 = 70 \, \text{nS}$ 15 = 15 nS $80 = 80 \, \text{nS}$ 20 = 20 nS

The numbers and coding on this page do not include all variations available, but are shown as examples of the most widely used variations. Contact Accutek if other information is required.



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### **EXAMPLES:**

#### AK581024ASP-60

1 Meg x 8, Dynamic RAM, Leadless SIM, Page Mode, Commercial, 60 nSEC Access Time

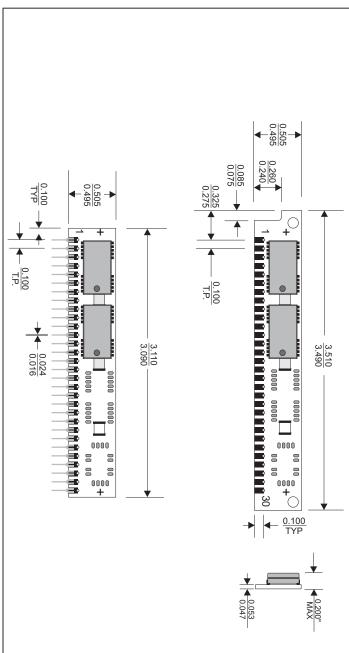
#### AK581024AGP-70

1 Meg x 8, Dynamic RAM, Leaded SIP, Page Mode Commercial, 70 nSEC AccessTime

### **MECHANICAL DIMENSIONS**



5 6 7 8



Accutek reserves the right to make changes in specifications at any time and without notice. Accutek does not assume any responsibility for the use of any circuitry described; no circuit patent licenses are implied. Preliminary data sheets contain minimum and maximum limits based upon design objectives, which are subject to change upon full characterization over the specific operating conditions.